

HIGH PERFORMANCE TRIACS

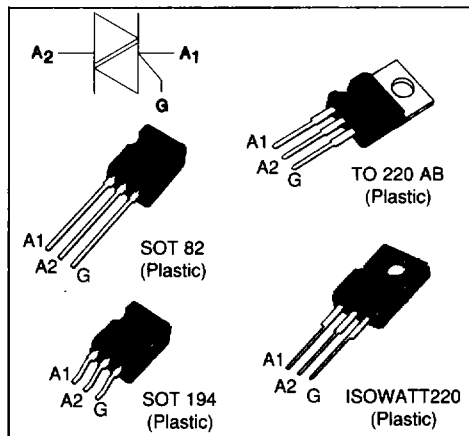
IN DEVELOPMENT

FEATURES

- $I_{T(RMS)} = 8\text{ A}$
- $V_{DRM} = 400\text{ V to } 800\text{ V}$
- SENSITIVE GATE : $I_{GT} \leq 10\text{ mA}$
- HIGH COMMUTATION : $(di/dt)_c > 7\text{ A/ms}$ without snubber

DESCRIPTION

The T810 / T835 high voltage TRIAC Families are high performance planar diffused PNPN devices glass passivated technology. Packaged either in TO 220 AB, SOT 82, SOT 194 and ISOWATT220 these products are intended for all bi-directional switch applications.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (360° conduction angle)	TO 220 AB	$T_c = 110\text{ °C}$	8	A
		SOT 194/SOT 82			
		ISOWATT220	$T_c = 100\text{ °C}$		
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25°C)		$t_p = 8.3\text{ ms}$	65	A
			$t_p = 10\text{ ms}$	60	
i_{2t}	i_{2t} value		$t_p = 10\text{ ms}$	18	A _{2s}
di/dt	Critical rate of rise of on-state current Gate supply : $I_G = 100\text{ mA}$ $di_G/dt = 1\text{ A/}\mu\text{s}$		Repetitive $F = 50\text{ Hz}$	10	A/ μs
			Non Repetitive	50	
T_{stg} T_j	Storage and operating junction temperature range			- 40 to + 125	°C
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T_l	Maximum lead temperature for soldering during 10 s at 4.5 mm from case			230	°C

Symbol	Parameter	T810 or T835				Unit
		-400	-600	-700	-800	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125\text{ °C}$	400	600	700	800	V